

SEMICONDUCTOR PLANE LUMINESCENCE DEVICE WITH METAL REFLECTION CAVITY

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- European:

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Abstract of CN85104012

As circuit substrate of this device, double faced copper-foil plate is used, the front face being gold plated and the frame of reflection cavity being made of plastics as ABS. The plastics surface is plated with a layer of metal with excellent thermal conductivity such as chromium plating. The inner wall of the frame is further plated with a silver layer and the metal reflection cavity thus constructed is of enhanced heat-radiation efficiency and reflection efficiency. The tube core density of the luminescence diodes inserted on the substrate can be increased and the luminosity is also increased. This invention can be widely used for information display under high illumination condition for military, industrial and communication purposes .

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